
Semiconductor Wafer Bonding: Science, Technology, and Applications 16

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Table of Contents

Preface *iii*

Chapter 2 G01 – Fundamentals and Characterization

Impact of an Amino-Alcohol Organic Molecule on SiO₂ and Si Bonding Energy 3
F. Fournel, A. Calvez, V. Larrey, G. Eleouet, C. Morales, F. Rieutord

Interfacial Analysis of Plasma Fusion Bonded Interfaces Under Various Bonding Conditions by Neutron Reflectometry 11
M. Fujino, K. Takahashi, K. Kikuchi, N. Miyata, T. Yoshida, T. Miyazaki

Hetero-Integration of β -Ga₂O₃ and Diamond Substrates by Hydrophilic Bonding Technique 17
T. Matsumae, Y. Kurashima, H. Takagi, H. Umezawa, K. Tanaka, T. Ito, H. Watanabe, E. Higurashi

Characterization of Silicon Carbon Nitride for Low Temperature Wafer-to-Wafer Direct Bonding 21
F. Nagano, S. Iacovo, A. Phommahaxay, F. Inoue, E. Sleenckx, S. De Gendt, G. Beyer, E. Beyne

Direct Wafer Bonding Methods: A Practical Process Selection Guide 33
V. Dragoi, B. Rebhan, E. Pabo

Investigation of Post-Bond Distortion in Direct Wafer Bonding 47
N. Ip, A. Nagata, N. Kohama, N. Wada, K. Motoda

Chapter 3 G01 – Adhesive and Temporary Bonding

<i>(Invited)</i> Parylene C Based Adhesive Bonding on 6" and 8" Wafer Level for the Realization of Highly Reliable and Fully Biocompatible Microsystems <i>F. Selbmann, M. Baum, C. Meinecke, M. Wiemer, T. Otto, Y. Joseph</i>	55
--	----

Adhesive Wafer Bonding Using Ultra-Thin Spray-Coated BCB Layers <i>J. Rimböck, J. Gasiorowski, M. Pires, T. Zenger, J. Burggraf, V. Dragoi</i>	67
---	----

Chapter 4

G01 – Surface Activated and Low Temperature Wafer Bonding

Ion Species Dependence on the Interfacial Properties of Silicon Homojunctions Bonded Using an Ion Bombardment Treatment <i>M. E. Liao, K. Huynh, T. Bai, C. Flötgen, M. S. Goorsky</i>	81
---	----

200 mm Ge Wafer Production for Oxide-Free Si-Ge Direct Wafer Bonding <i>B. Rebhan, J. Vanpaemel, V. Dragoi</i>	87
---	----

Chapter 5

G01 – Wafer Bonding for Sensors and MEMS

The Role of Wafer Edge in Wafer Bonding Technologies <i>R. Knechtel, U. Schwarz, S. Dempwolf, A. Nevin, H. Klingner, G. Lindemann, M. Schikowski</i>	103
---	-----

Chapter 6

G01 – Si, Ge, and III-V Wafer Bonding

III-V Thin-Film Solar Cells Bonded to Si Substrates via Metal Grids <i>T. Hishida, J. Liang, N. Shigekawa</i>	117
--	-----

Nanostructural Investigation on GaAs//Indium Tin Oxide/Si Junctions for III-V-on-Si Hybrid Multijunction Cells <i>T. Hara, J. Liang, K. Araki, T. Kamioka, H. Sodabanlu, K. Watanabe, M. Sugiyama, N. Shigekawa</i>	125
--	-----

Silicon Direct Bonding for the European Space Agency's Next X-ray Observatory	135
<i>R. Günther, M. Collon, G. Vacanti, N. Barrière, B. Landgraf, M. Vervest, B. Okma, L. Voruz, L. Keek, L. Babic, A. Bayerle, A. Thete, D. Girou, E. Hauser, G. M. Serrano, N. Eenkhoorn, R. van der Hoeven, A. Chatbi, S. Verhoeckx, R. Visser, D. Maks, P. da Silva Ribeiro, M. Bavdaz, E. Wille, I. Ferreira</i>	

Chapter 7

G01 – Hybrid and 3D Bonding

(Invited) Hybrid Wafer Bonding – The Fusion of Low Temperature Dielectric and Metal Bonding Technologies	145
<i>S. N. Farrens</i>	
Epitaxial Growth of Active Si on Top of SiGe Etch Stop Layer in View of 3D Device Integration	157
<i>R. Loo, A. Jourdain, G. Rengo, C. Porret, A. Y. Hikavy, M. Liebens, L. Becker, P. Storck, G. Beyer, E. Beyne</i>	
Fabrication of 3-Layer Stacked Pixel for Pixel-Parallel CMOS Image Sensors by Au/SiO ₂ Hybrid Bonding of SOI Wafers	167
<i>M. Goto, N. Nakatani, Y. Honda, T. Watabe, M. Nanba, Y. Iguchi, T. Saraya, M. Kobayashi, E. Higurashi, H. Toshiyoshi, T. Hiramoto</i>	
Collective Die Bonding: An Enabling Toolkit for Heterogeneous Integration	173
<i>J. Burggraf, T. Uhrmann, M. Pires</i>	

Chapter 8

G01 – Packaging and Metal Bonding

Selective Heat Input for Low Temperature Metallic Wafer Level Bonding	183
<i>M. Wiemer, C. Hofmann, K. Vogel</i>	
Ar/N ₂ Plasma Induced Metastable Cu _x N _y for Cu-Cu Direct Bonding	203
<i>L. Hu, S. C. K. Goh, C. S. Tan</i>	
Gas Absorption in Package Using Au/Pt/Ti Bonding Layer	211
<i>T. Matsumae, S. Kariya, Y. Kurashima, H. Takagi, M. Hayase, E. Higurashi</i>	

Layer Configurations for Al-Ge Eutectic Wafer Bonding <i>J. Visker, L. Peng, S. Kang, B. Vereecke, L. Haspeslagh</i>	217
Author Index	223